

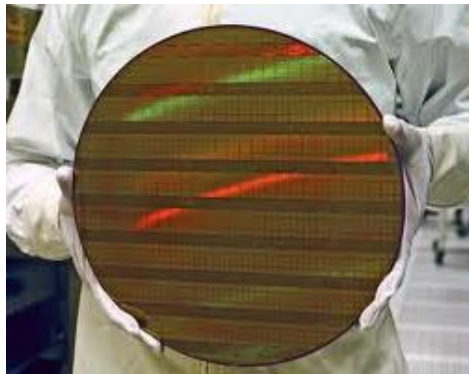
Large Area Electronic Materials

Micro vs. Macro

Microelectronics: e.g. NVIDIA GB202:
5 nm lithography TSMC
92 B Transistors on 750 mm² die



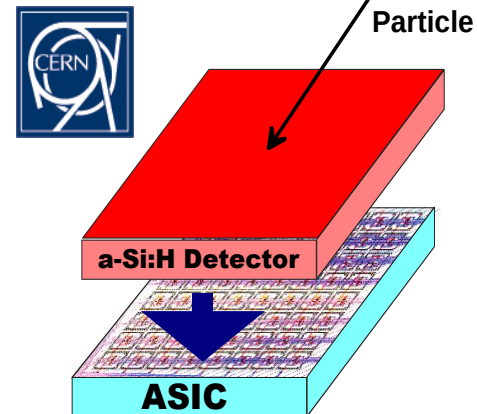
600 cm² wafer (12")



Macroelectronics:
e.g. TFT displays
Sharp 8M-B120C (120")
4.01 m² (2.6 m x 1.5 m)
33 Mio pix (7680x4320)



Particle detectors

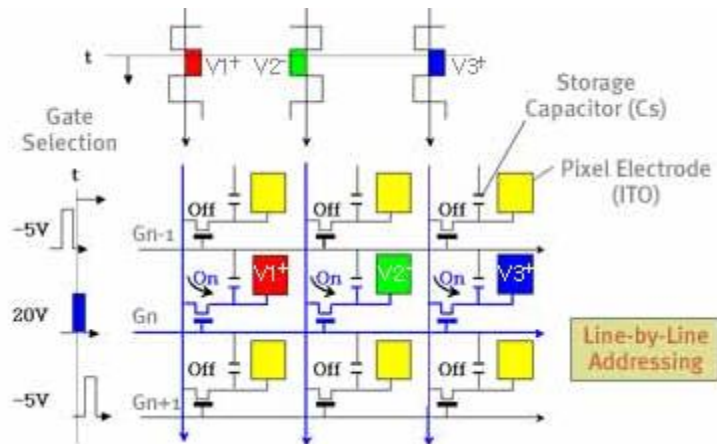
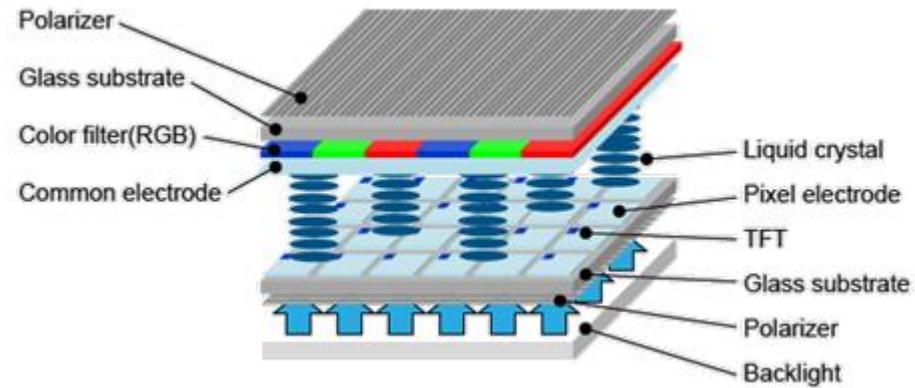


x-ray imagers



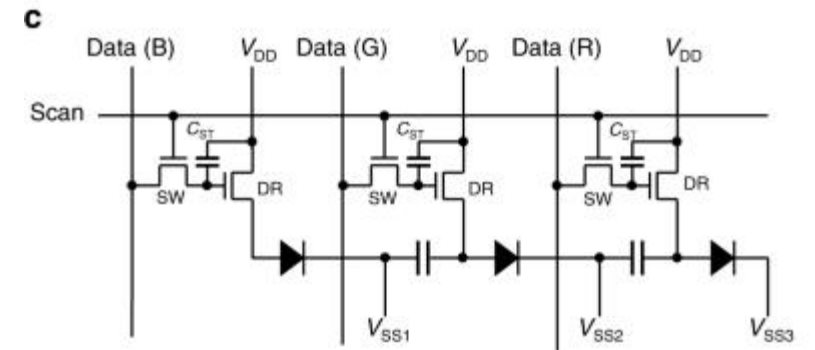
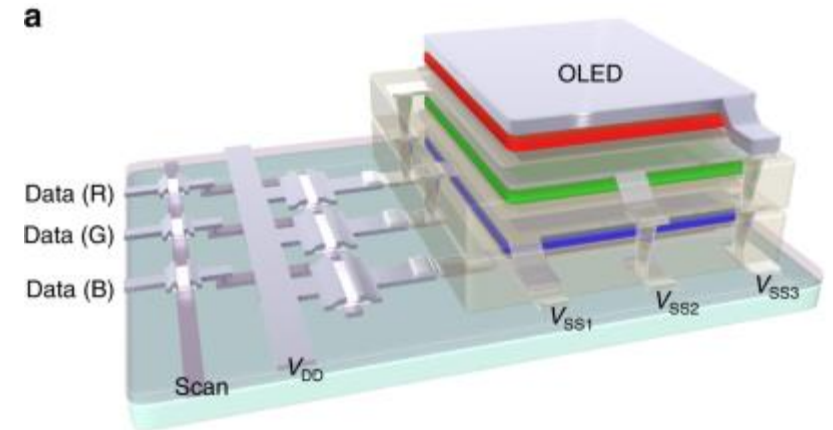
What's inside?

Liquid crystal display (LCD)



source: j-display.com / rose-hulman.edu

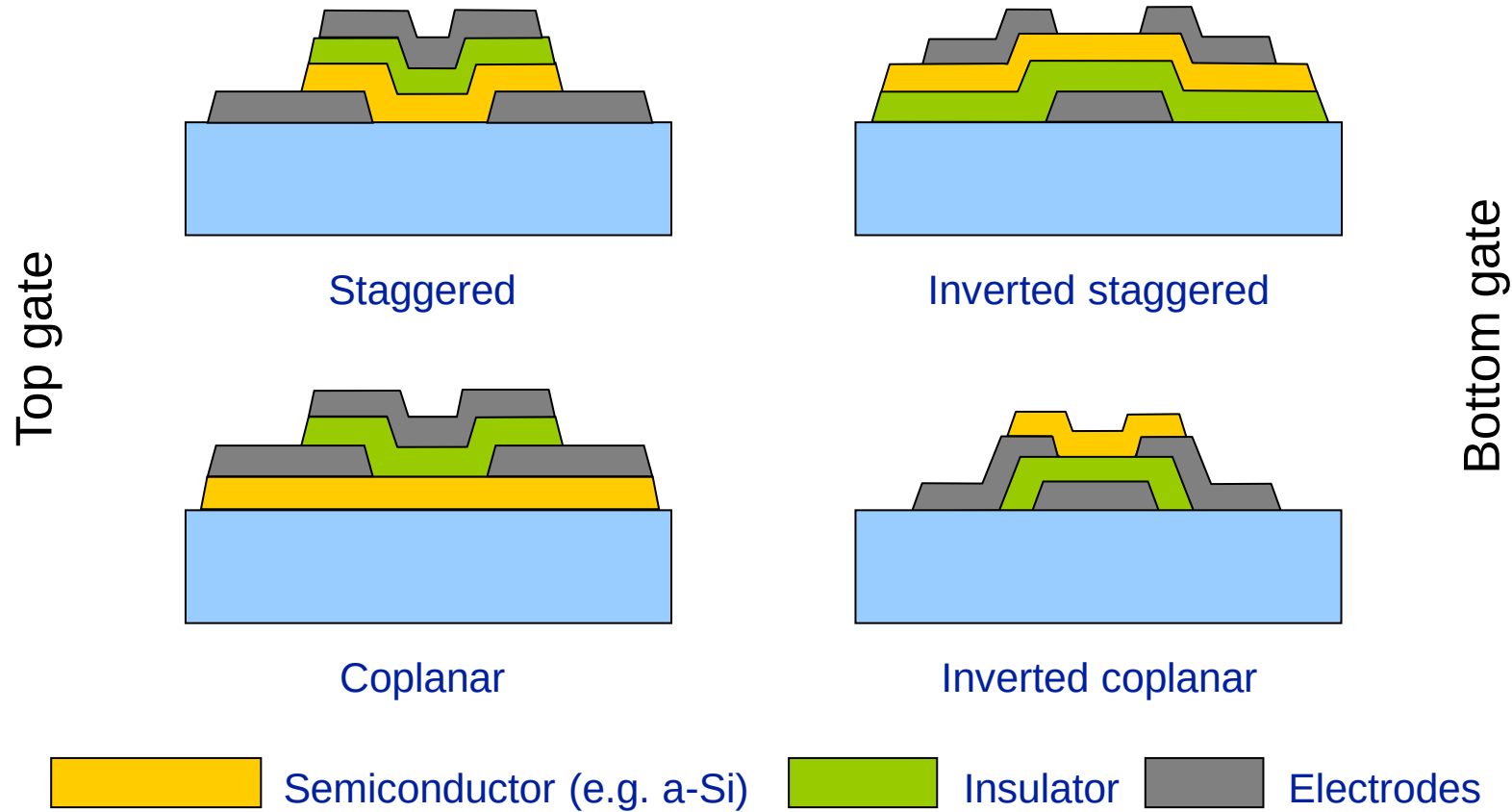
Organic light emitting diode (OLED)



source: Choi, Nature communications 11 (2020)

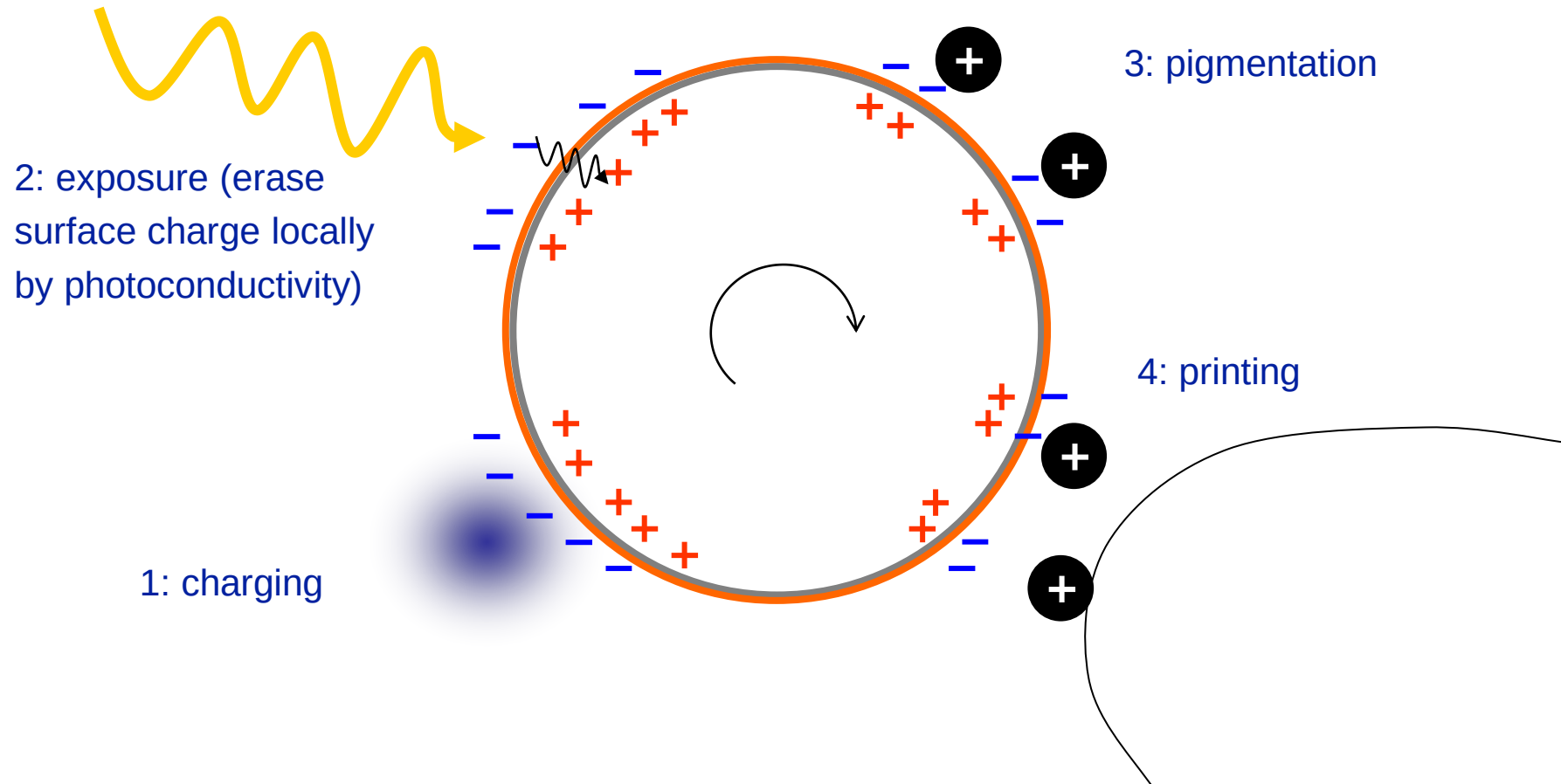
What's inside?

TFT displays: thin film transistor, switch on/off each pixel



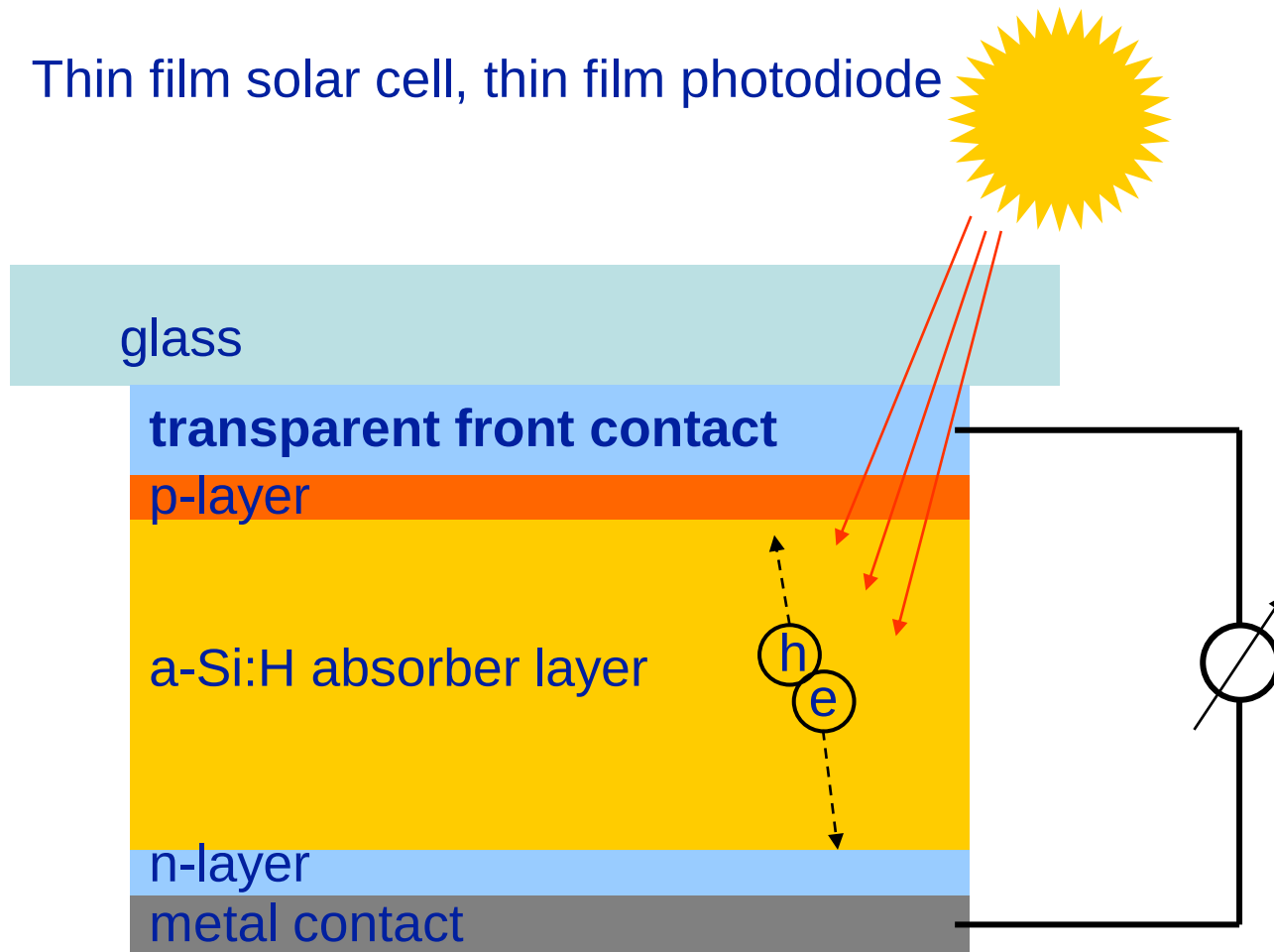
What's inside?

Photocopier: photoconductive coating on printing drum



What's inside?

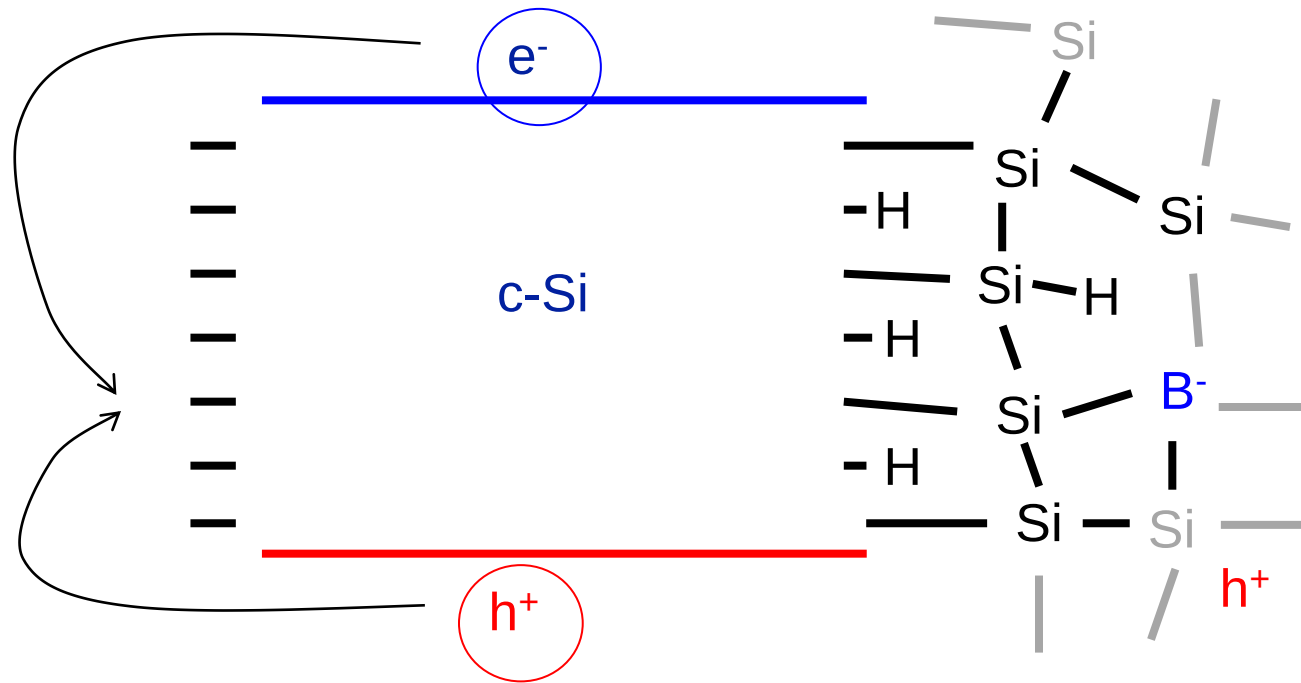
Thin film solar cell, thin film photodiode



e.g. Tissot Solar Touch, Garmin Fenix

What's inside?

Heterojunction solar cell*: passivation **and** contact layers



* used in current world record silicon solar cells, 26.8% (Longi)

Which materials work on large area?

- a-Si:H, a-Se, a-As₂Se₃, organic semiconductors: Xerography (photoconduction)
- a-Si:H: TFT (channel), solar cells (absorber)
- a-Si₃N₄: TFT (gate insulator)
- a-SiC:B, nc-SiOx:B, etc: (transparent p-type contacts)
- a-Si_{1-x}Ge_x:H, μ c-Si:H: solar cells (low gap absorbers)
- Chalcopyrites (Cu,In,Ga,Se,S compounds): solar cells (absorber)
- CdTe, CdS: solar cells (absorber)
- ZnS, InP, etc: display, lighting
- Metal oxides: transparent contacts
(remember c-Si: max wafer size 12")

Emerging materials

- Organic semiconductors: OLED, TFT (channel), electroluminescent displays, solar cells
- Metal oxides: TFT (gate insulator and channel), sensors



19" transparent AMOLED (Samsung, 2011)



71 cm x 56 cm, CeeLite

How to grow thin films of these materials?

Thin film manufacturing: core of today's semiconductor industry

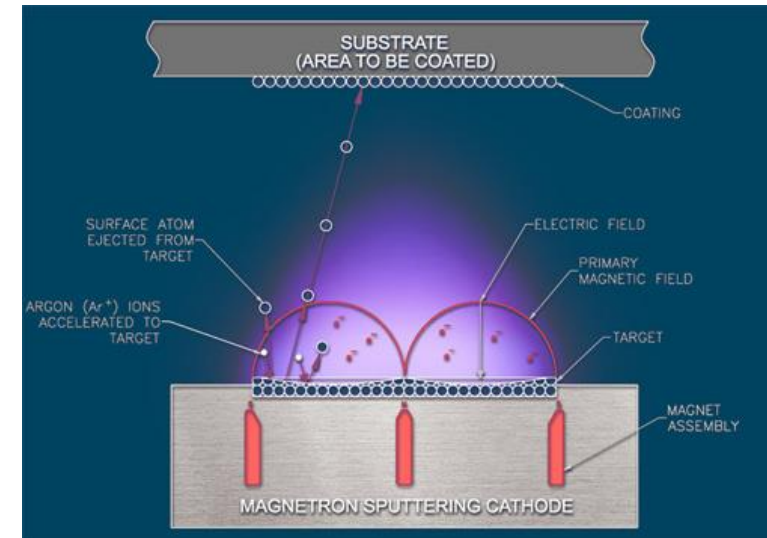
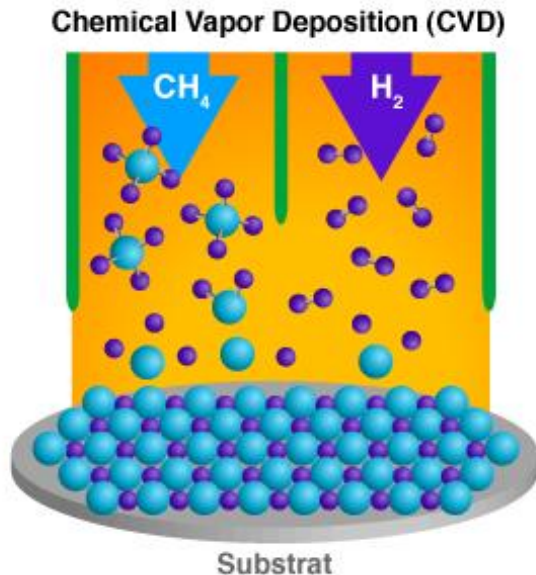
Chemical processes

Use of volatile precursors (fluid or gas) which react at the surface of a substrate.

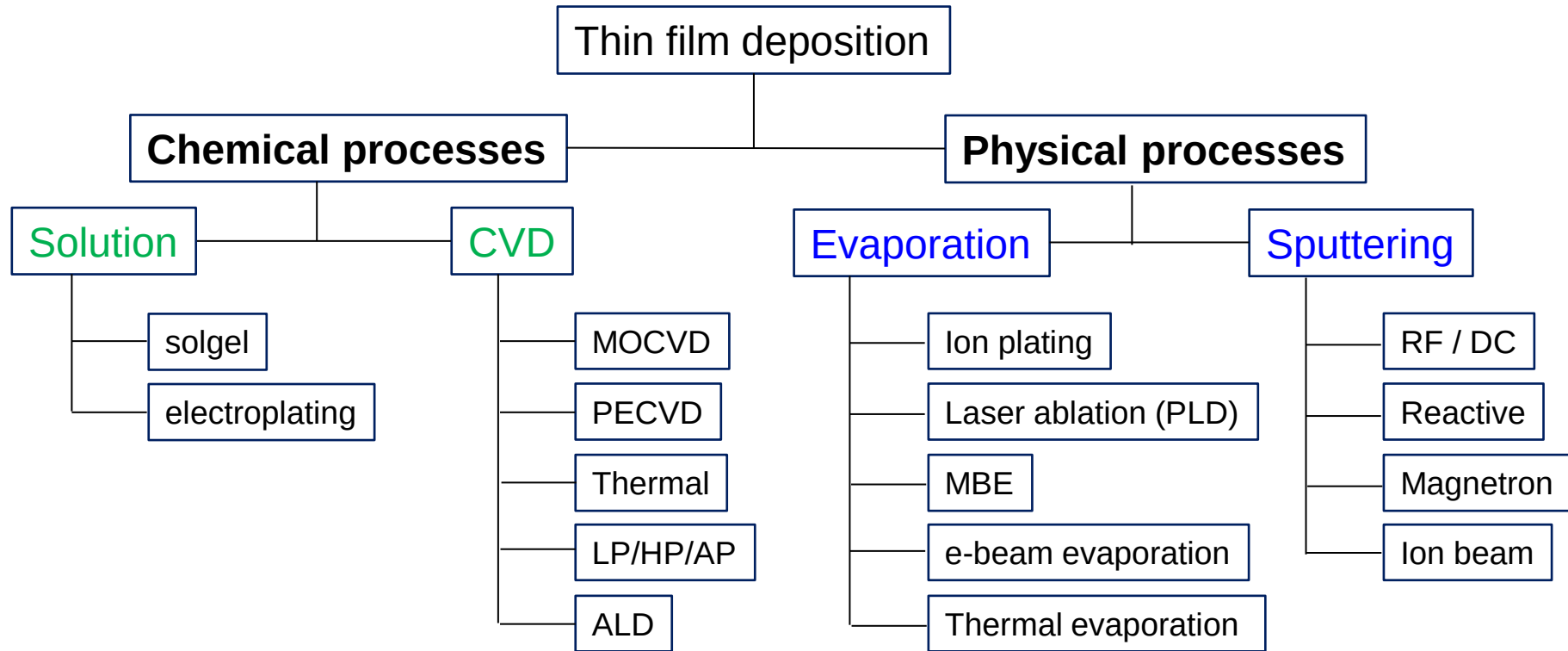
Thin film deposition

Physical processes

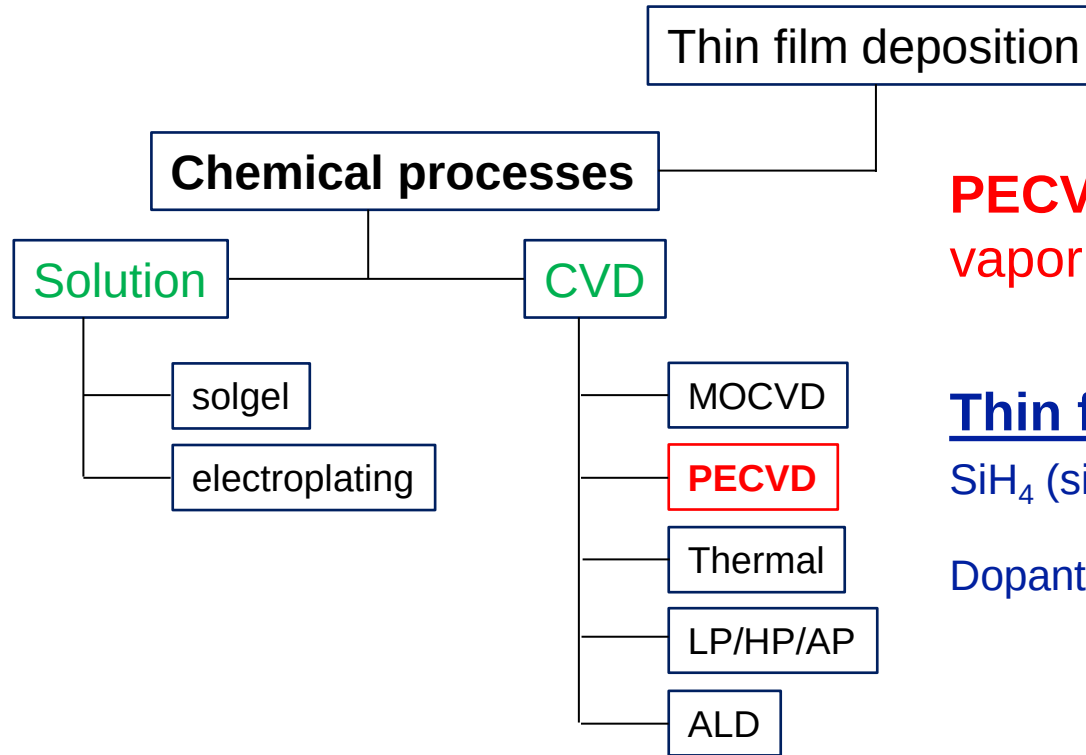
Release from a source and deposition on a substrate using e.g. mechanical or thermodynamic processes.



How to grow thin films of these materials?

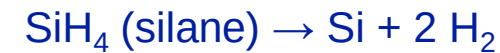


How to grow thin films of these materials?

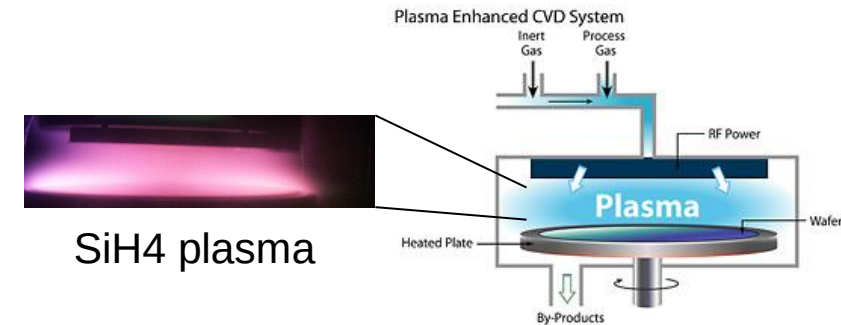


PECVD: plasma enhanced chemical vapor deposition

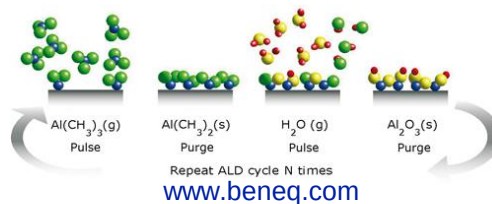
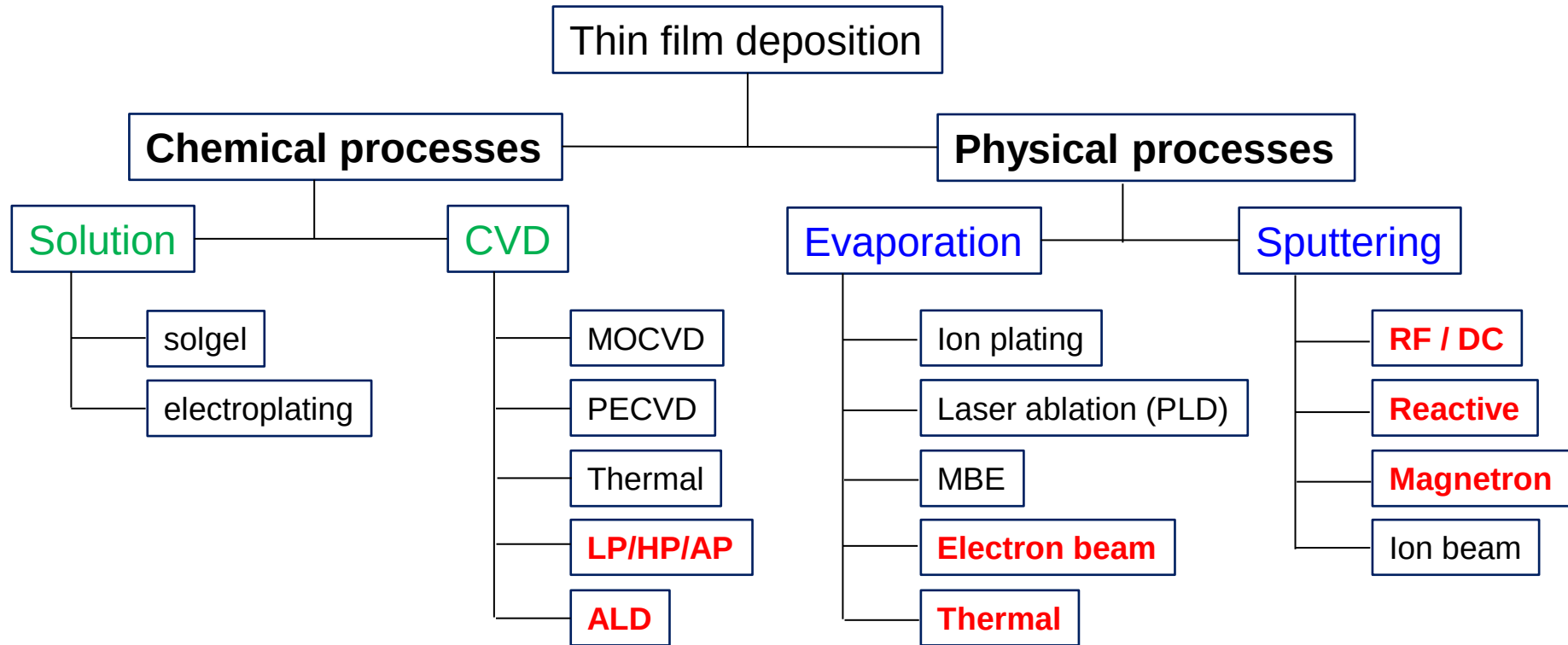
Thin film silicon:



Dopants: PH_3 (phosphine) or B_2H_6 (di-borane)

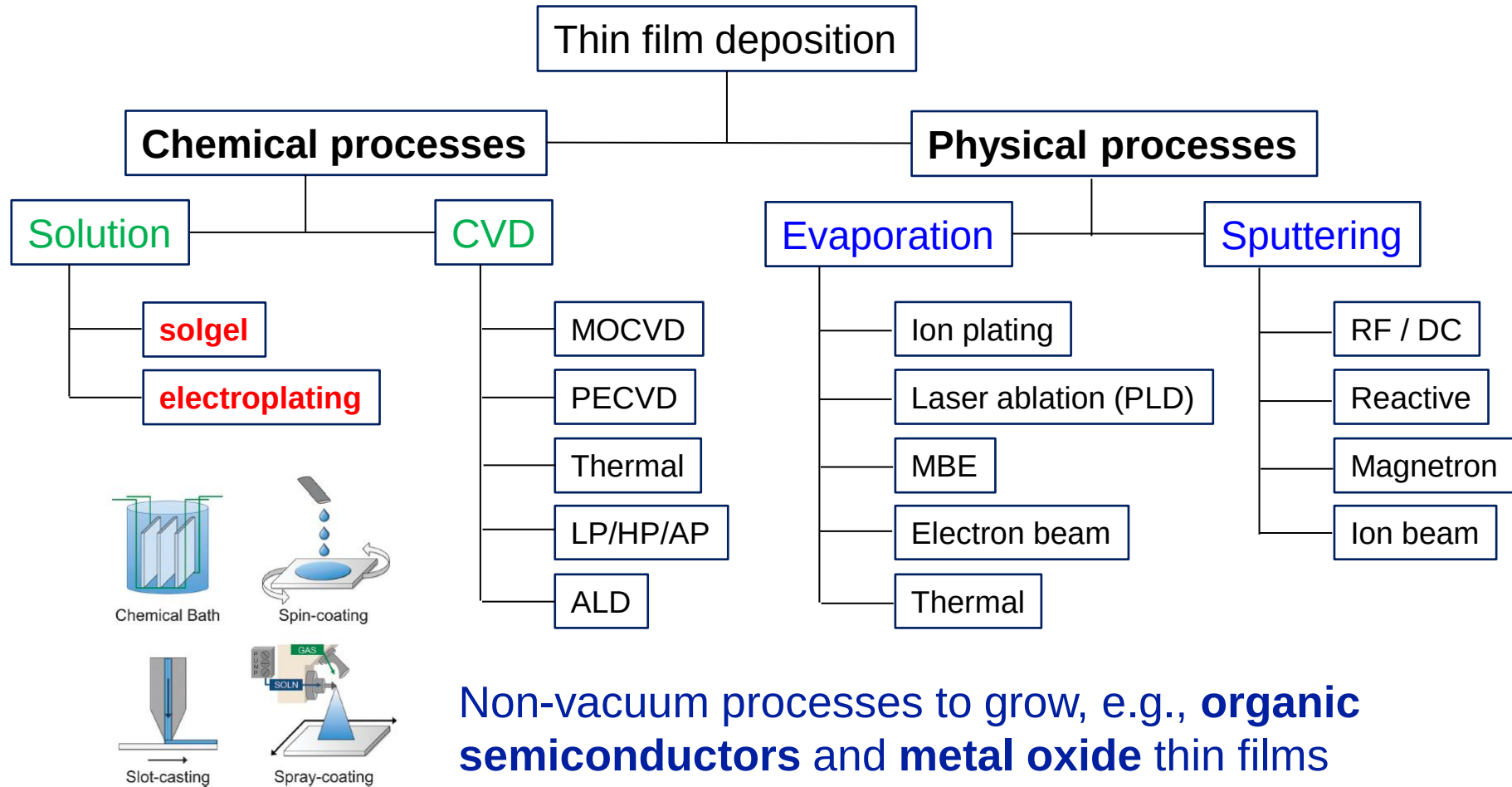


How to grow thin films of these materials?

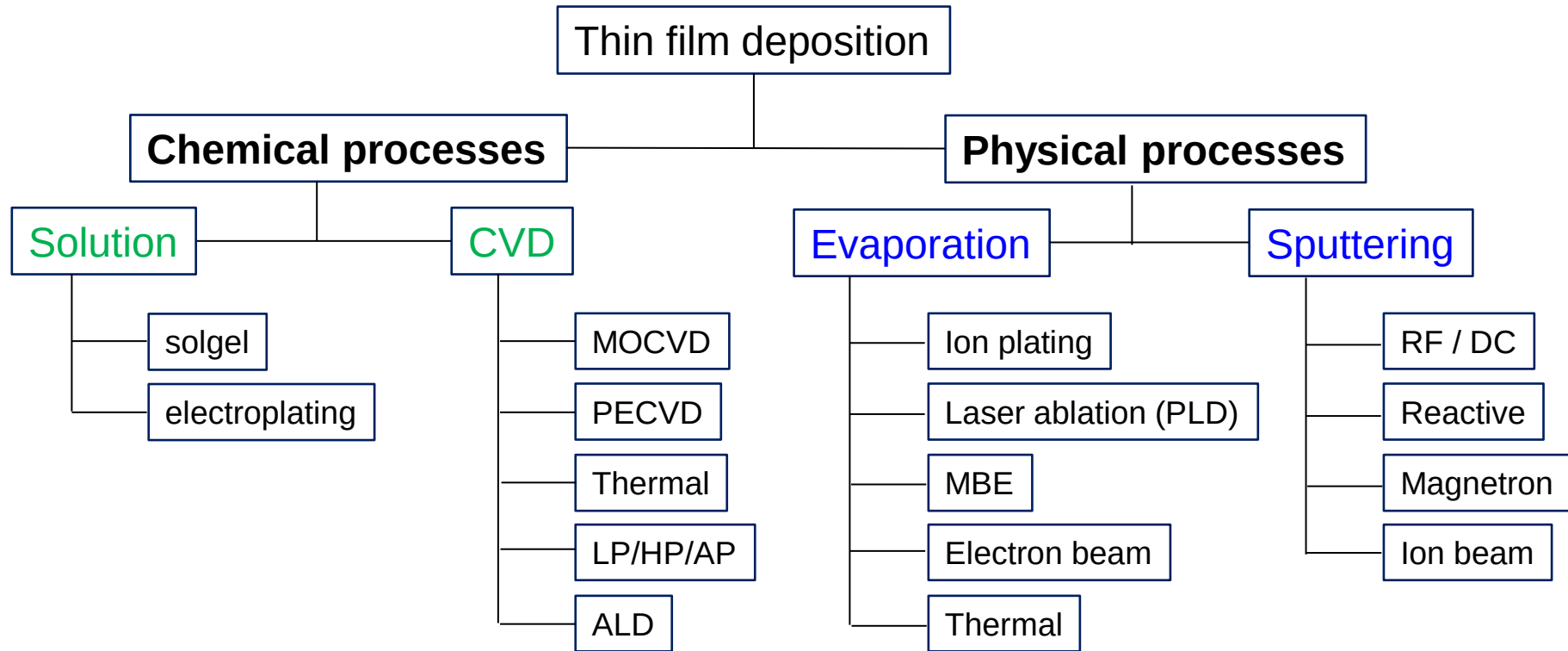


Vacuum processes to grow, e.g.,
metal and **metal oxide** thin films

How to grow thin films of these materials?



How to grow thin films of these materials?



Up-scalable techniques?

Scalability



	Gen 2	Gen 3 / 3.5	Gen 4	Gen 5	Gen 5	Gen 5.5	Gen 6	Gen 7 / 7.5	Gen 8
1st Release	2/ '93~	4/ '95~	1/ '00~	8/ '01~	6/ '02~	8/ '04~	5/ '03~	7/ '04~	2006
System Layout									
Model	1600	3500 / 4300 / 4300A	5500/5500A	10K	15K / 15KA	20K	25K / 25KA	40K / 40KA	50K
Substrate Size (mm)	370x470 400x500	550x650 600x720 620x750	680x880 730x920	1000x1200	1100x1250 1200x1300	1300x1500	1500x1800 1500x1850	1870x2200 1950x2250	2160x2460
Substrate Area	2,000 cm ² (1.00)	4,650 cm ² (2.33 from 1600)	6,716 cm ² (1.44 from 4300)	12,000 cm ² (1.79 from 5500)	15,600 cm ² (1.30 from 10K)	19,500 cm ² (1.25 from 15 K)	27,750 cm ² (1.78 from 15 K)	41,140 cm ² (1.52 from 25 K)	53,136 cm ² (1.21 from 40 KA)
Panel size Inch	10.4	12.1	15 ~ 17	19 ~ 23	21 ~ 24	32W	37W	46W	52W
Panel/sub	4	6	6	6	6	6	6	6	6
Application	Note PC ----->			Monitor ----->		TV			

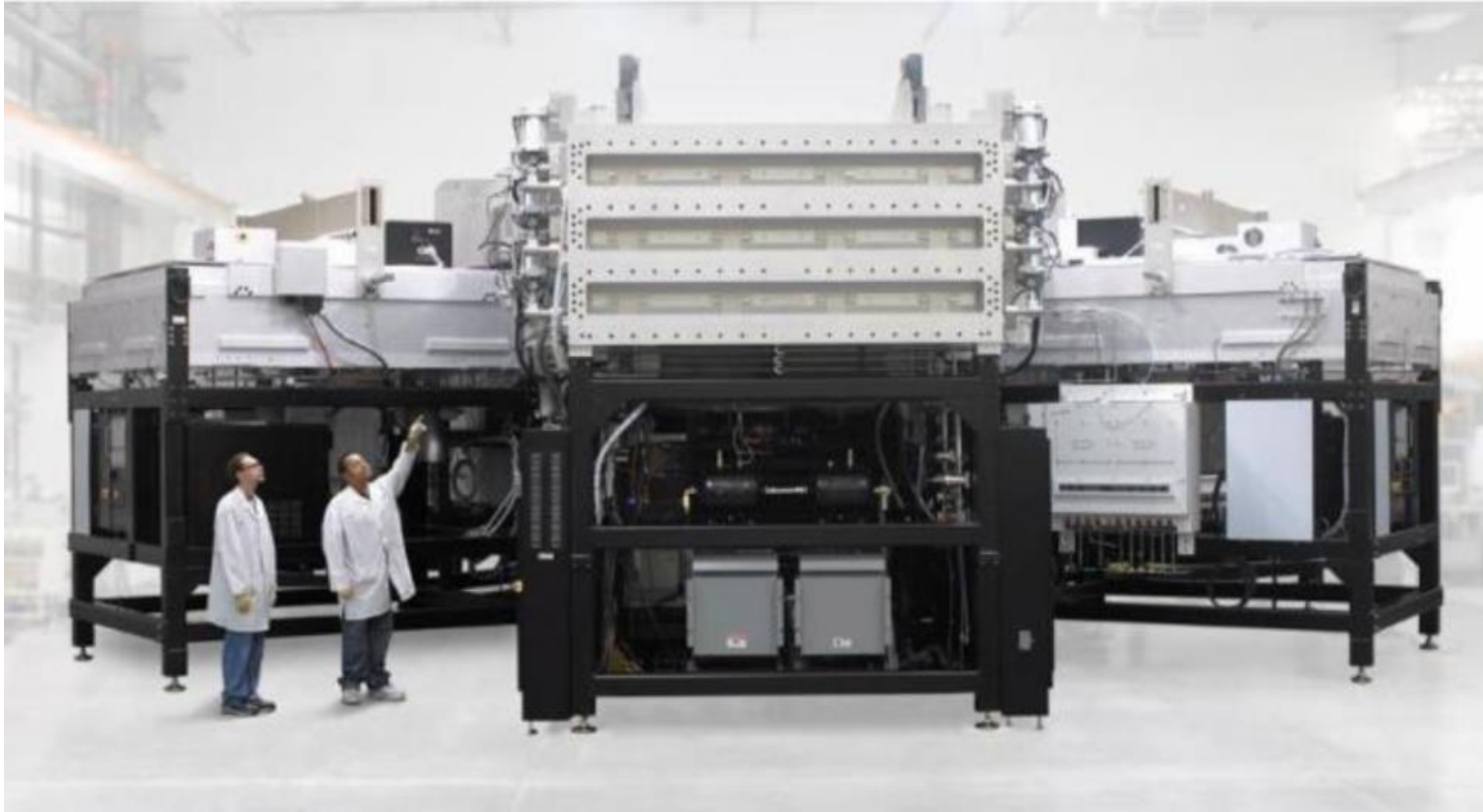
Gen10

(remember:
15": 304x228 mm²)

Source: Applied Materials

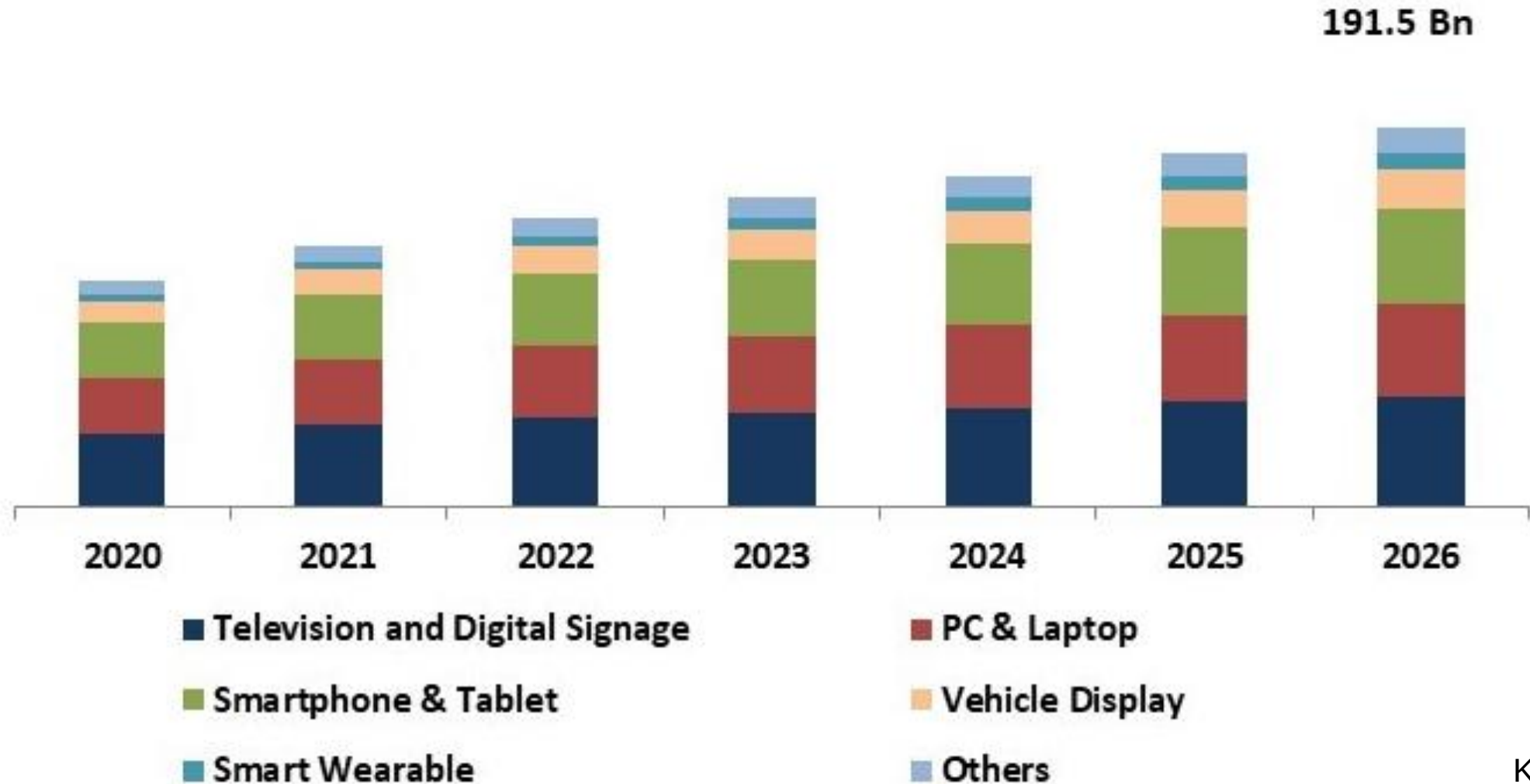
Examples

Gen10 (9 m²)
PECVD cluster
(AMAT AKT90)



Other suppliers: Leybold, Jusung, Ulvac, etc.

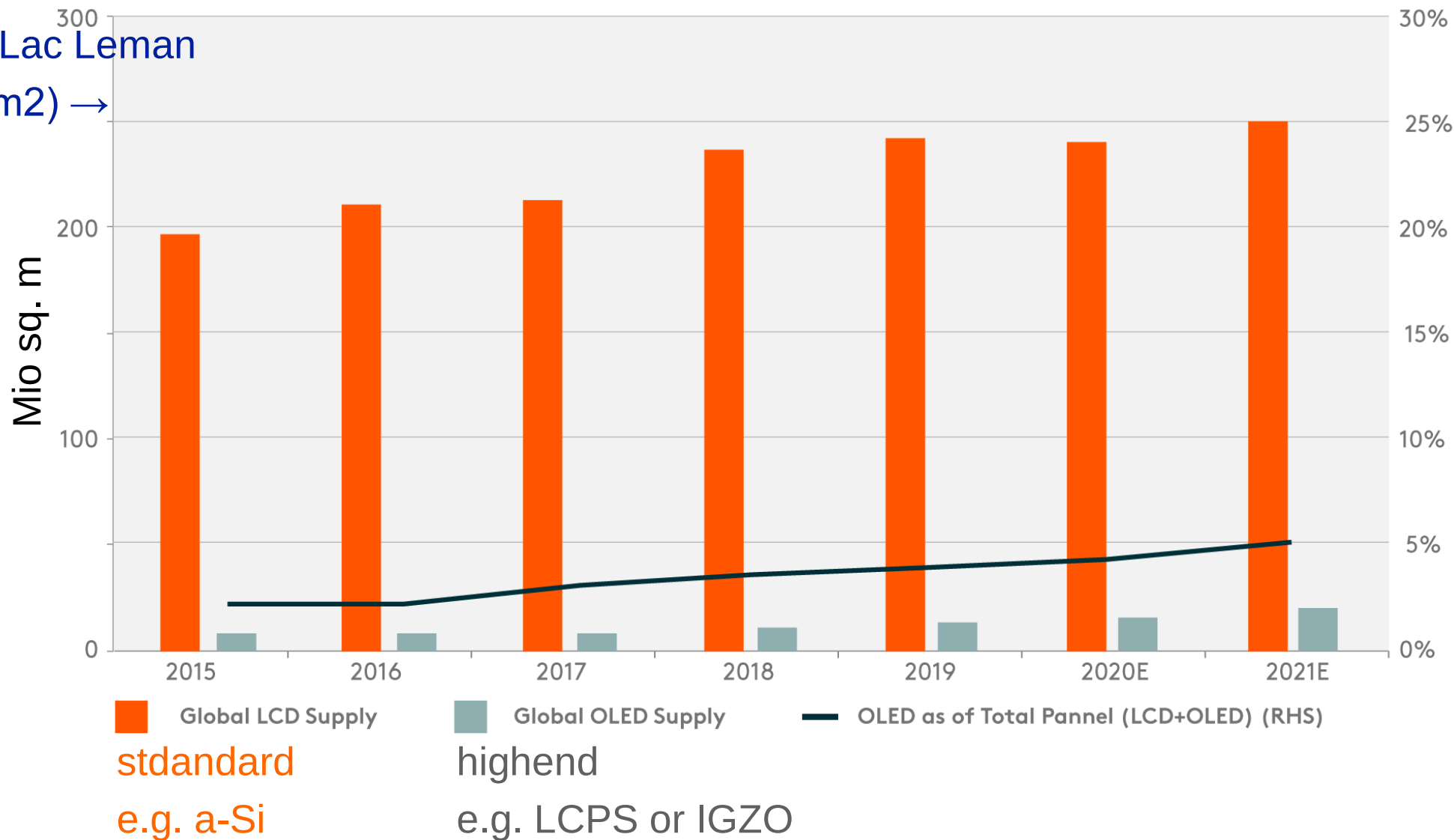
Global display market



strong growth forecasted for vehicle displays

Prospect of TF-Si

half of Lac Lemans
(580 km²) →



MorganStanley
July 2020

From micro- to macroelectronics

Benefits

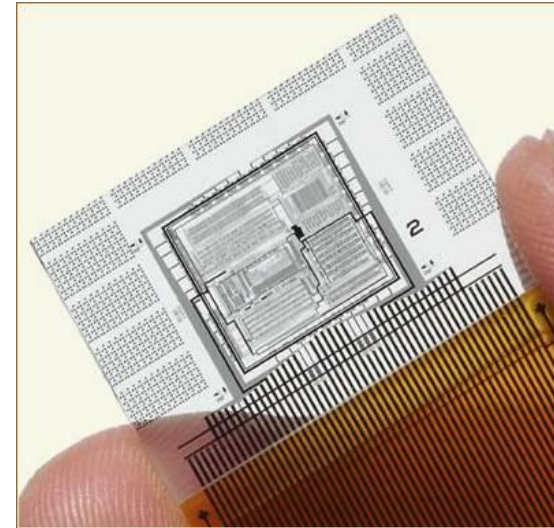
- Large area fabrication
- Lower processing costs (thin film deposition/coating, printing)
- Device stacking, 3D integration
- Combination of technologies

Drawbacks

- Process control, non uniformity
- Lower material quality (low mobility, defects,..)
- Lower device performance
- Non standard equipment

Driving forces

- Lower cost
 - Replace «classical electronics/devices» by deposited or printed devices
- Larger devices
 - Equipment scale-up
 - Printing
- New devices / applications
 - Flat panel displays/imagers
 - System on panel
 - Flexible devices



Z80 CPU on glass substrate,
13'000 TFT, Sharp



Samsung Galaxy Z
foldable screen

Challenge of a-Si channel material

- a-Si is not a unique material
 - only PECVD delivers “good a-Si”
 - properties depend on power/temperature during deposition
- a-Si contains defects (always!)
 - low carrier mobility => TFTs can switch voltages, not currents
 - shallow trap states => TFT channels become conductive only after all defects are filled
 - deep defects act as recombination centres => limited minority carrier transport in solar cells
- a-Si is metastable
 - solar cells: light induced defects (note: effect saturates)
 - TFTs: threshold voltage shift (take care in device design)

Workaround: laser-crystallized poly-Si (LCPS), In-Ga-Zn-O (IGZO)

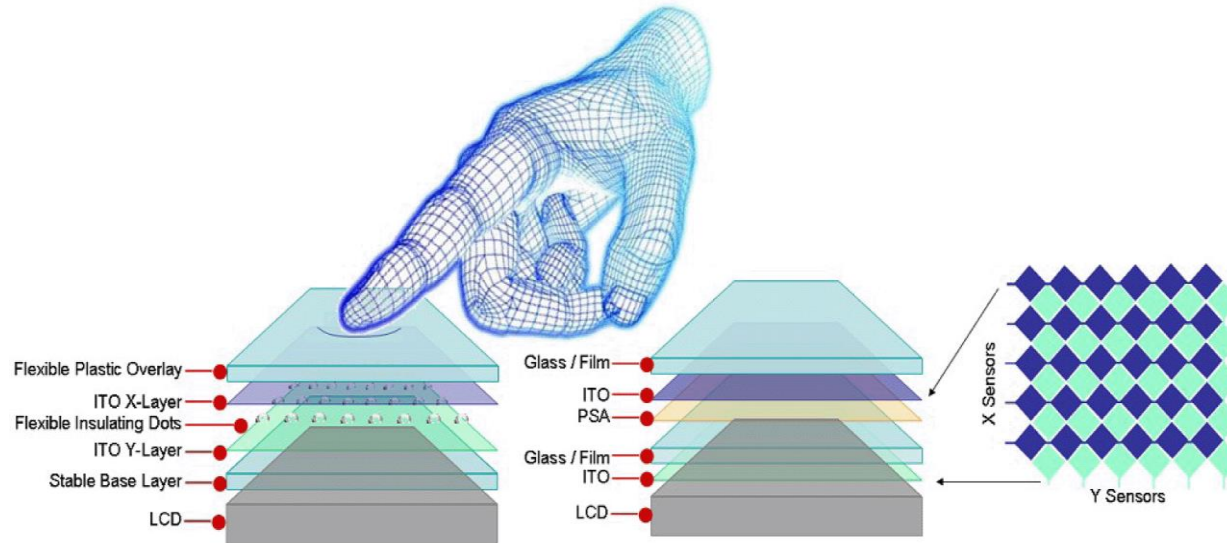
Transparent Conducting Oxides (TCOs)

Materials that transmit light and conduct electrical current simultaneously

- ✓ Semiconducting
- ✓ dopable (n-type)
- ✓ Wide band gap
- ✓ Transparent in the VIS and NIR

Application:
Transparent electrode in
optoelectronic devices

Use of TCOs: e.g. in touch screens



Source: <http://www.digikey.com>

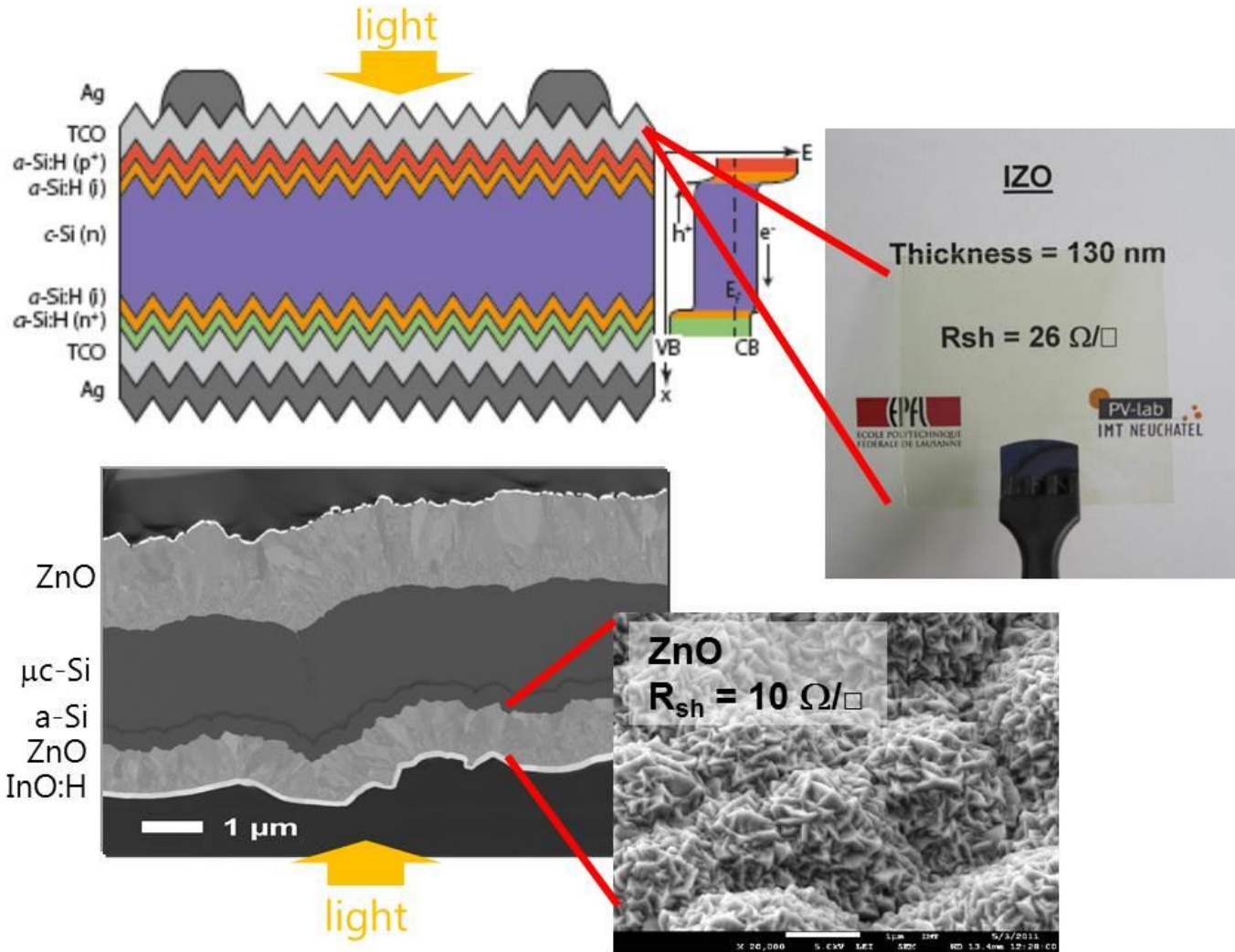
TCO functionality / requirement

Capacitive detection:
need for conductive layer.

Light should go out of the screen:
need for transparent layer.



Use of TCOs: e. g. in solar cells



Front TCO requirements

Let the light into the solar cells with minimum losses.

- **Low optical absorptance in the UV to red-IR region of the spectrum**

Collection and transport of the photo-generated electron and holes

- **High electrical conductivity**

$$\sigma = eN\mu$$

TCOs: where is the challenge?

- ✓ Transparency-conductivity trade off
 - ✓ Increase carrier density limits transmittance in the NIR-IR.
 - ✓ Ideally need to increase mobility instead of carrier density to improve conductivity.

$$\uparrow (\sigma) = eN\mu \uparrow$$

- ✓ Defects:
 - ✓ Limits electron mobility
 - ✓ Subgap defects: limits transmittance (Vis). Limits TFTs device performance (flexible transparent TFTs).
- ✓ Properties strongly dependent on deposition conditions:
 - ✓ Macroscopic to point defects
 - ✓ Deposition on large area
 - ✓ Process compatibility with devices (e.g. high T process)